ON5088

NPN wideband silicon germanium RF transistor

Rev. 3 — 12 December 2012

Product data sheet

1. Product profile

1.1 General description

NPN silicon germanium microwave transistor for high speed, low noise applications in a plastic, 4-pin dual-emitter SOT343F package.

CAUTION



This device is sensitive to ElectroStatic Discharge (ESD). Observe precautions for handling electrostatic sensitive devices.

Such precautions are described in the ANSI/ESD S20.20, IEC/ST 61340-5, JESD625-A or equivalent standards.

1.2 Features and benefits

- Low noise high gain microwave transistor
- High maximum stable gain 27 dB at 1.8 GHz
- 110 GHz f_T silicon germanium technology

1.3 Applications

- 2nd and 3rd LNA stage in DBS LNBs
- Satellite radio
- Low noise amplifiers for microwave communications systems
- WLAN and WiMAX applications
- Analog/digital cordless applications

1.4 Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
V_{CB}	collector-base voltage	open emitter		-	-	10	V
V_{CE}	collector-emitter voltage	open base		-	-	3.0	V
		shorted base		-	-	10	V
V_{EB}	emitter-base voltage	open collector		-	-	1.0	V
I _C	collector current			-	25	40	mΑ
P _{tot}	total power dissipation	T _{sp} ≤ 90 °C	[1]	-	-	136	mW
h _{FE}	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V};$ $T_j = 25 \text{ °C}$		160	280	400	
C_{CBS}	collector-base capacitance	$V_{CB} = 2 \text{ V}; f = 1 \text{ MHz}$		-	70	-	fF



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Table 1. Quick reference data ...continued

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
f_{T}	transition frequency	I_C = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C	-	55	-	GHz
G _{p(max)}	maximum power gain	$I_C = 25 \text{ mA}; V_{CE} = 2 \text{ V};$ f = 12 GHz; $T_{amb} = 25 \text{ °C}$	[2] _	13	-	dB
NF	noise figure	I_C = 5 mA; V_{CE} = 2 V; f = 12 GHz; Γ_S = Γ_{opt} ; T_{amb} = 25 °C	-	1.1	-	dB

^[1] T_{sp} is the temperature at the solder point of the emitter lead.

2. Pinning information

Table 2. Discrete pinning

Pin	Description	Simplified outline	Graphic symbol
1	emitter		
2	base	3 4	4
3	emitter		2 —
4	collector	2 1	1, 3 mbb159

3. Ordering information

Table 3. Ordering information

Type number	Package		
	Name	Description	Version
ON5088	-	plastic surface-mounted flat pack package; reverse pinning; 4 leads	SOT343F

4. Marking

Table 4. Marking

Type number	Marking	Description
ON5088 *6N		* = p : made in Hong Kong
		* = t : made in Malaysia
		* = W : made in China

^[2] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)}$ = Maximum Stable Gain (MSG).

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5. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{CB}	collector-base voltage	open emitter	-	10	V
V_{CE}	collector-emitter voltage	open base	-	3.0	V
		shorted base	-	10	V
V_{EB}	emitter-base voltage	open collector	-	1.0	V
I _C	collector current		-	40	mA
P _{tot}	total power dissipation	$T_{sp} \le 90 ^{\circ}C$	<u>[1]</u> _	136	mW
T _{stg}	storage temperature		-65	+150	°C
Tj	junction temperature		-	150	°C

^[1] T_{sp} is the temperature at the solder point of the emitter lead.

6. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions	Тур	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point		440	K/W

7. Characteristics

Table 7. Characteristics

 $T_j = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
$V_{(BR)CBO}$	collector-base breakdown voltage	$I_C = 2.5 \mu A; I_E = 0 \text{ mA}$	10	-	-	V
$V_{(BR)CEO}$	collector-emitter breakdown voltage	$I_C = 1 \text{ mA}$; $I_B = 0 \text{ mA}$	3.0	-	-	V
I _C	collector current		-	25	40	mΑ
I _{CBO}	collector-base cut-off current	$I_E = 0 \text{ mA}; V_{CB} = 4.5 \text{ V}$	-	-	100	nΑ
h _{FE}	DC current gain	$I_C = 10 \text{ mA}; V_{CE} = 2 \text{ V}$	160	280	400	
C _{CES}	collector-emitter capacitance	V _{CB} = 2 V; f = 1 MHz	-	268	-	fF
C _{EBS}	emitter-base capacitance	V _{EB} = 0.5 V; f = 1 MHz	-	400	-	fF
C _{CBS}	collector-base capacitance	$V_{CB} = 2 \text{ V}; f = 1 \text{ MHz}$	-	70	-	fF
f _T	transition frequency	I_C = 25 mA; V_{CE} = 2 V; f = 2 GHz; T_{amb} = 25 °C	-	55	-	GHz
G _{p(max)}	maximum power gain	I_C = 25 mA; V_{CE} = 2 V; T_{amb} = 25 °C	[1]			
		f = 1.8 GHz	-	27	-	dB
		f = 12 GHz	-	13	-	dB
$ s_{21} ^2$	insertion power gain	I_C = 25 mA; V_{CE} = 2 V; T_{amb} = 25 °C				
		f = 1.8 GHz	-	25.4	-	dB
		f = 12 GHz	-	9.3	-	dB

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Table 7. Characteristics ...continued $T_i = 25$ °C unless otherwise specified.

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
NF noise figure		I_C = 5 mA; V_{CE} = 2 V; Γ_S = Γ_{opt} ; T_{amb} = 25 °C				
	f = 1.8 GHz	-	0.43	-	dB	
	f = 12 GHz	-	1.1	-	dB	
G _{ass} associated gain		I_C = 5 mA; V_{CE} = 2 V; Γ_S = Γ_{opt} ; T_{amb} = 25 °C				
	f = 1.8 GHz	-	22	-	dB	
		f = 12 GHz	-	10	-	dB
P _{L(1dB)}	output power at 1 dB gain compression	$\rm I_C$ = 25 mA; $\rm V_{CE}$ = 2 V; $\rm Z_S$ = $\rm Z_L$ = 50 $\rm \Omega$; $\rm T_{amb}$ = 25 °C; f = 1.8 GHz	-	9	-	dBm
IP3	third-order intercept point	I_C = 25 mA; V_{CE} = 2 V; Z_S = Z_L = 50 Ω ; T_{amb} = 25 °C; f_2 = f_1 + 1 MHz; f_1 = 1.8 GHz	-	17	-	dBm

^[1] $G_{p(max)}$ is the maximum power gain, if K > 1. If K < 1 then $G_{p(max)} = MSG$.

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8. Package outline

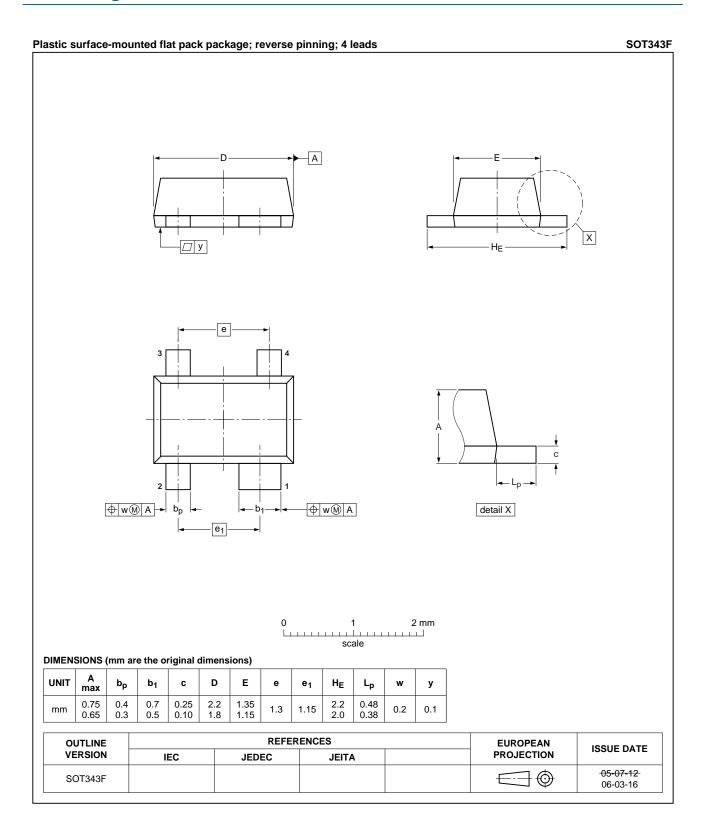


Fig 1. Package outline SOT343F

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9. Abbreviations

Table 8. Abbreviations

Acronym	Description
DBS	Direct Broadcast Satellite
DC	Direct Current
DRO	Dielectric Resonator Oscillator
LNA	Low Noise Amplifier
LNB	Low Noise Block
NPN	Negative-Positive-Negative
RF	Radio Frequency
WLAN	Wireless Local Area Network
WiMAX	Worldwide Interoperability for Microwave Access

10. Revision history

Table 9. Revision history

Document ID	Release date	Data sheet status	Change notice	Supersedes
ON5088 v.3	20121212	Product data sheet	-	ON5088 v.2
Modifications:	• Table 1 on p	age 1: some changes have be	en made.	
	 Table 5 on p 	age 3: some changes have be	en made.	
	 Table 7 on p 	age 3: The minimum value for	V _{(BR)CEO} has been o	changed.
ON5088 v.2	20111222	Product data sheet	-	ON5088 v.1
ON5088 v.1	20100422	Product data sheet	-	-

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11. Legal information

11.1 Data sheet status

Document status[1][2]	Product status[3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
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